

isc Silicon PNP Power Transistor

2SB989

DESCRIPTION

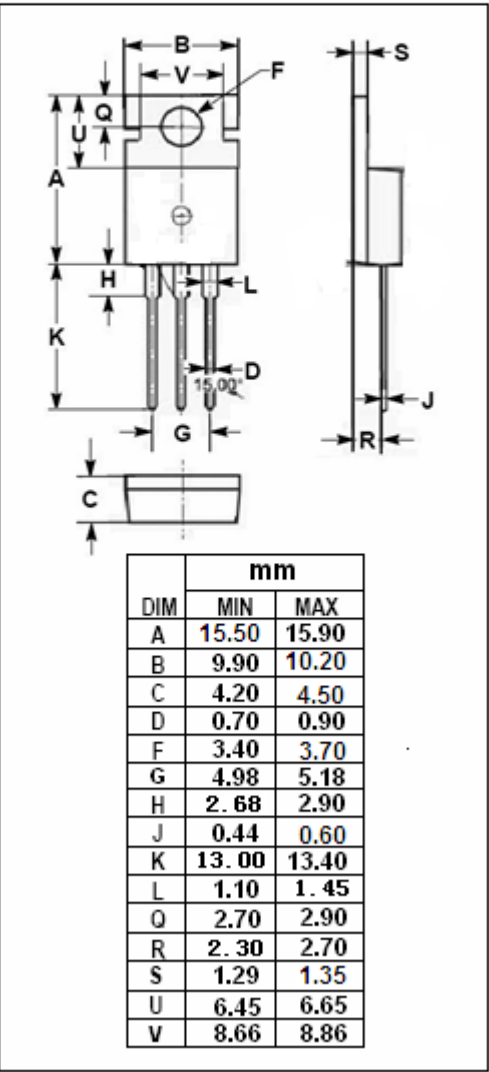
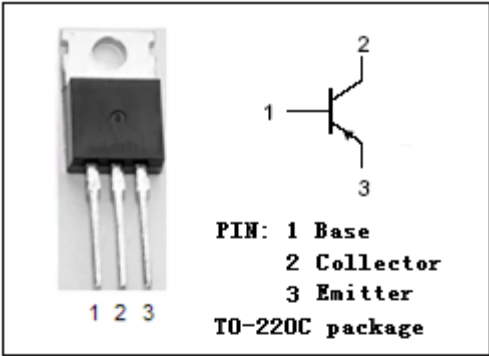
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -80V(\text{Min})$
- Collector Power Dissipation-
: $P_C = 30W@ T_C = 25^{\circ}C$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -1.7V(\text{Max})@ (I_C = -3A, I_B = -0.3A)$
- Complement to Type 2SD1352

APPLICATIONS

- Designed for general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-80	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-4	A
I_B	Base Current-Continuous	-0.4	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}C$	30	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SB989****ELECTRICAL CHARACTERISTICS**T_j=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; I _B = 0	-80			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -3A; I _B = -0.3A			-1.7	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -3A; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-30	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-100	μ A
h _{FE-1}	DC Current Gain	I _C = -0.5A; V _{CE} = -5V	40		240	
h _{FE-2}	DC Current Gain	I _C = -3A; V _{CE} = -5V	15			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f _{test} = 1MHz		90		pF
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -5V		8		MHz

◆ **h_{FE-1} Classifications**

R	O	Y
40-80	70-140	120-240